

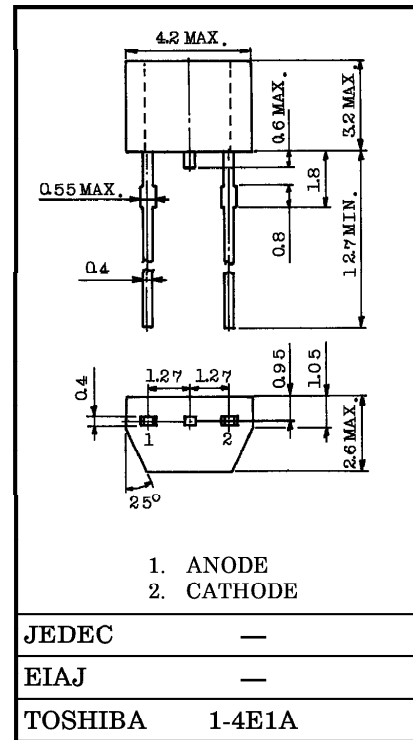
TOSHIBA VARIABLE CAPACITANCE DIODE SILICON EPITAXIAL PLANAR TYPE

# 1SV101

FM TUNER APPLICATIONS.

Unit in mm

- High Capacitance Ratio :  $C_{3V} / C_{9V} = 2.0 \sim 2.7$
- Low Series Resistance :  $r_s = 0.3 \Omega$  (Typ.)
- Small Package.
- Low Tuning Voltage Range : 3V-9V



MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	$V_R$	15	V
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55~125	$^\circ\text{C}$

Weight : 0.9g

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	$V_R$	$I_R = 10 \mu\text{A}$	15	—	—	V
Reverse Current	$I_R$	$V_R = 15\text{V}$	—	—	10	nA
Capacitance	$C_{3V}$	$V_R = 3\text{V}, f = 1\text{MHz}$	28	—	32	pF
Capacitance	$C_{9V}$	$V_R = 9\text{V}, f = 1\text{MHz}$	12	—	14	pF
Capacitance Ratio	$C_{3V} / C_{9V}$	—	2.0	—	2.7	
Series Resistance	$r_s$	$C = 30\text{pF}, f = 50\text{MHz}$	—	0.3	0.5	$\Omega$

Note: Units are compounded in one package and are matched to 3%.

$$\frac{C(\text{Max.}) - C(\text{Min.})}{C(\text{Min.})} \leq 0.03 \quad (V_R = 3\text{V}-9\text{V})$$

and capacitance is classified as Table 1.

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Table 1 : Address classification of capacitance  
 TEST CONDITION : f = 1MHz, Ta = 25°C

Unit : pF

No.	C <sub>3V</sub>	C <sub>5V</sub>	C <sub>7V</sub>	C <sub>9V</sub>
1	28.20~29.04	20.50~21.11	15.65~16.11	12.066~12.427
2	28.85~29.71	20.97~21.59	16.01~16.49	12.343~12.713
3	29.51~30.39	21.44~22.08	16.38~16.87	12.627~13.005
4	30.19~31.09	21.94~22.59	16.76~17.26	12.917~13.304
5	30.89~31.81	22.45~23.12	17.15~17.66	13.214~13.610
6		22.97~23.65	17.54~18.06	13.518~13.923
7		23.49~24.19	17.94~18.47	

- (1) The capacitance value of address classification is shown with confidence to at least  $\pm 0.5\%$  accuracy.
- (2) The address is specified in the compounded package (or label).

Example      4 - 3 - 2 - 1  
 (C<sub>3V</sub>) (C<sub>5V</sub>) (C<sub>7V</sub>) (C<sub>9V</sub>)

